BTA216X series D, E and F

GENERAL DESCRIPTION

Passivated guaranteed commutation triacs in a full pack, plastic envelope intended for use in motor control circuits or with other highly inductive loads. These devices balance the requirements of commutation performance and gate sensitivity. The "sensitive gate" E series and "logic level" D series are intended for interfacing with low power drivers, including micro controllers.

PINNING - SOT186A

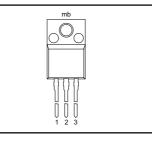
QUICK REFERENCE DATA

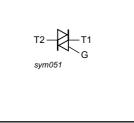
SYMBOL	PARAMETER	MAX.	UNIT
	BTA216X- BTA216X- BTA216X- BTA216X-	600D 600E 600F	
V _{DRM}	Repetitive peak off-state voltages RMS on-state current	600	V
I _{T(RMS)} I _{TSM}	Non-repetitive peak on-state current	16 140	A A

PIN CONFIGURATION

SYMBOL

PIN	DESCRIPTION		
1	main terminal 1		
2	main terminal 2		
3	gate		
case	isolated		





LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
	Repetitive peak off-state voltages		-	600 ¹	v
I _{T(RMS)}	RMS on-state current	full sine wave; T _{hs} ≤ 38 °C	-	16	А
I _{⊤SM} I²t dI _⊤ /dt	Non-repetitive peak on-state current I ² t for fusing Repetitive rate of rise of on-state current after	full sine wave; $T_j = 25$ °C prior to surge t = 20 ms t = 16.7 ms t = 10 ms $I_{TM} = 20 A$; $I_G = 0.2 A$; $dI_G/dt = 0.2 A/\mu s$	- -	140 150 98 100	Α Α A²s A/μs
$\begin{array}{c} I_{GM} \\ P_{GM} \\ P_{G(AV)} \\ T_{stg} \\ T_{j} \end{array}$	triggering Peak gate current Peak gate power Average gate power Storage temperature Operating junction temperature	over any 20 ms period	- - -40 -	2 5 0.5 150 125	A W V C C

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 $A/\mu s$.

BTA216X series D, E and F

ISOLATION LIMITING VALUE & CHARACTERISTIC

 $T_{hs} = 25$ °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	R.M.S. isolation voltage from all three terminals to external heatsink	f = 50-60 Hz; sinusoidal waveform; R.H. ≤ 65% ; clean and dustfree	-	-	2500	V
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	10	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-hs} R _{th j-a}	Thermal resistance junction to heatsink Thermal resistance junction to ambient	full or half cycle with heatsink compound without heatsink compound in free air	- - -	- - 55	4.0 5.5 -	K/W K/W K/W

STATIC CHARACTERISTICS

$T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
		BTA216X-		D	E	F	
I _{GT}	Gate trigger current ²	$V_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$		_			
		T2+ G+ T2+ G-	-	5 5 5	10 10	25 25	mA mA
		T2-G-	-	5	10	25 25	mA
IL.	Latching current	$V_{D} = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$					
		T2+ G+ T2+ G-	-	15 25	25 30	30 40	mA mA
		T2- G-	-	25	30	40	mA
I _H	Holding current	V _D = 12 V; I _{GT} = 0.1 A	-	15	25	30	mA
					D, E, F		
V _T	On-state voltage	I _T = 20 A	-		1.5		V
V _{GT}	Gate trigger voltage	$V_{\rm D} = 12 \text{ V}; I_{\rm T} = 0.1 \text{ A}$	-		1.5		V
		$V_{D}^{r} = 400 \text{ V}; I_{T} = 0.1 \text{ A};$ $T_{i} = 125 \text{ °C}$	0.25		-		v
I _D	Off-state leakage current	$V_{\rm D} = V_{\rm DRM(max)}; T_{\rm j} = 125 ^{\circ}{\rm C}$	-		0.5		mA

² Device does not trigger in the T2-, G+ quadrant.

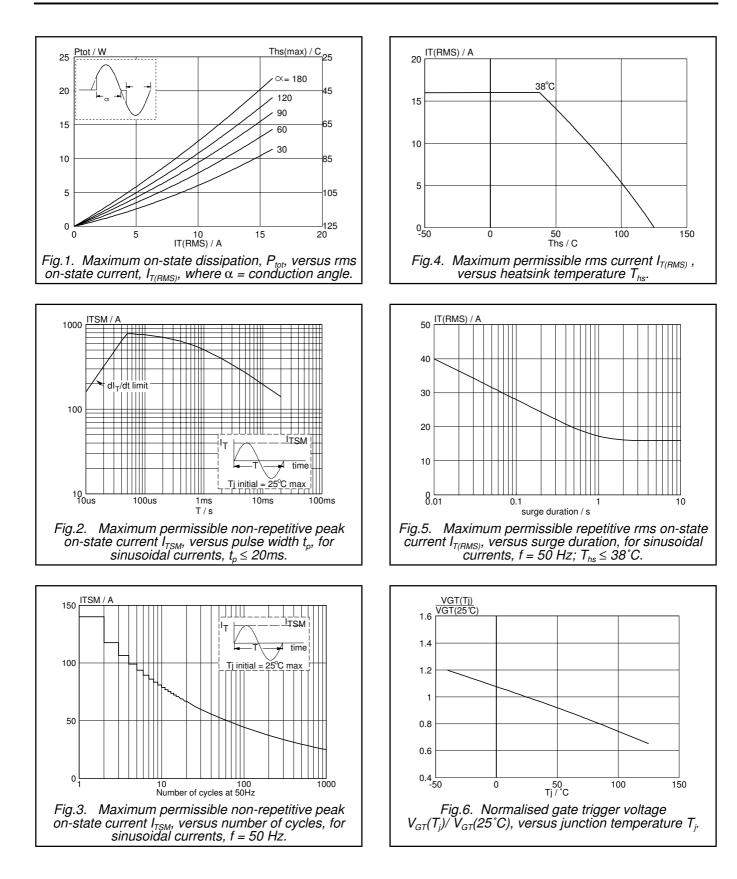
BTA216X series D, E and F

DYNAMIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.		MAX.	UNIT
		BTA216X-	D	E	F		
dV _D /dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)};$ $T_j = 110 \ ^{\circ}C; exponential$ waveform; gate open circuit	30	60	70	-	V/µs
dl _{com} /dt	Critical rate of change of commutating current	$V_{DM} = 400 \text{ V}; \text{T}_{j} = 125 ^{\circ}\text{C};$ $I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 10V/\mu \text{s}; \text{ gate}$ open circuit	2.5	6.2	18	-	A/ms
dl _{com} /dt	Critical rate of change of commutating current	$V_{\text{DM}} = 400 \text{ V}; \text{T}_{\text{j}} = 125 ^{\circ}\text{C}; \\ I_{\text{T(RMS)}} = 16 \text{ A}; \\ dV_{\text{com}}/dt = 0.1 \text{ V}/\mu\text{s}; \text{ gate} \\ \text{open circuit}$	12	20	50	-	A/ms

BTA216X series D, E and F



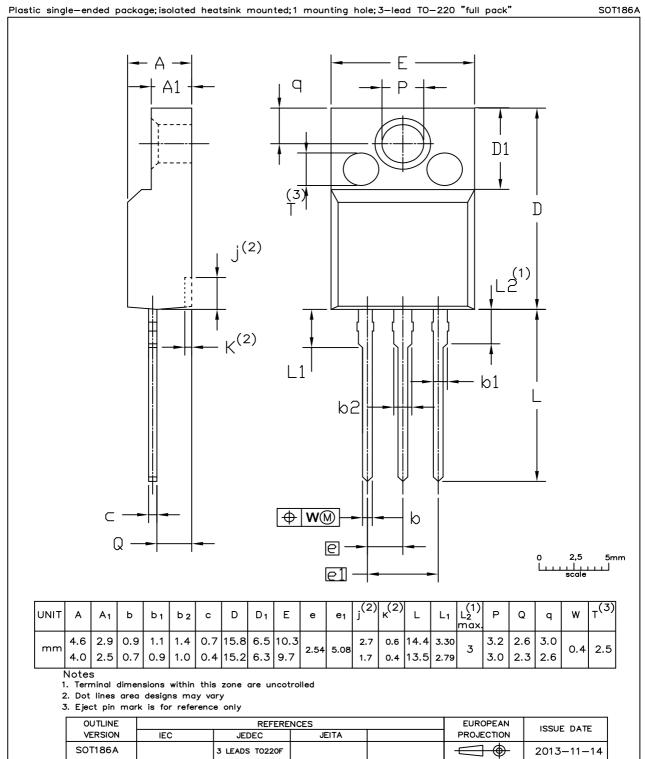
BTA216X series D, E and F

Three quadrant triacs guaranteed commutation

IT / A IGT(Tj) IGT(25℃) 50 Tj = 125 C Tj = 25 C 3 — T2+ G+ — T2+ Gtyp ma - T2- G-40 2.5 Vo = 1.195 V Rs = 0.018 Ohms 2 30 1.5 20 1 10 0.5 0 L 0 0 1.5 VT / V 150 0.5 2 2.5 3 -50 0 тј/℃ 100 1 Fig.7. Normalised gate trigger current $I_{GT}(T_j)/I_{GT}(25^{\circ}C)$, versus junction temperature T_{j} . Fig.10. Typical and maximum on-state characteristic. IL(Tj) IL(25°C) 10 Zth j-hs (K/W) 3 with heatsink compound without heatsink compound 25 1 2 0.1 1.5 - t_p 1 0.01 0.5 0.001 – 10us 0 -50 0.1ms 10ms 0.1s 1s 10s 50 Tj /℃ 1ms 0 100 150 tp/s Fig.11. Transient thermal impedance $Z_{th j-mb}$, versus Normalised latching current $I_L(T_i)/I_L(25^{\circ}C)$, Fig.8. versus junction temperature T_{i} pulse width $t_{\rm p}$. dlcom/dt (A/ms) IH(Tj) 100 3 IH(25°C F TYPE E TYPE D TYPE 2.5 2 10 1.5 1 0.5 1 0 -50 50 Tj /℃ 20 40 60 100 120 140 100 150 0 80 Tj/°C Fig.9. Normalised holding current $I_H(T_i)/I_H(25^{\circ}C)$, versus junction temperature T_j . Fig.12. Minimum, critical rate of change of commutating current dI_{com}/dt versus junction temperature, $dV_{com}/dt = 10V/\mu s$.

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MECHANICAL DATA



Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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